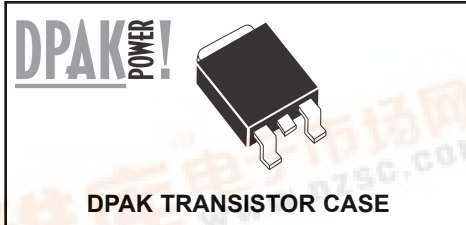


CJD31C NPN
CJD32C PNP
**COMPLEMENTARY SILICON
POWER TRANSISTOR**



Central™ Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD31C, CJD32C types are Complementary Silicon Power Transistors manufactured by the epitaxial base process, mounted in a surface mount package designed for power amplifier and high speed switching applications.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: (T_C=25°C unless otherwise noted)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Continuous Collector Current	I _C	3.0	A
Peak Collector Current	I _{CM}	5.0	A
Base Current	I _B	1.0	A
Power Dissipation	P _D	15	W
Power Dissipation (T _A =25°C)	P _D	1.56	W
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JC}	8.33	°C/W
Thermal Resistance	θ _{JA}	80.1	°C/W

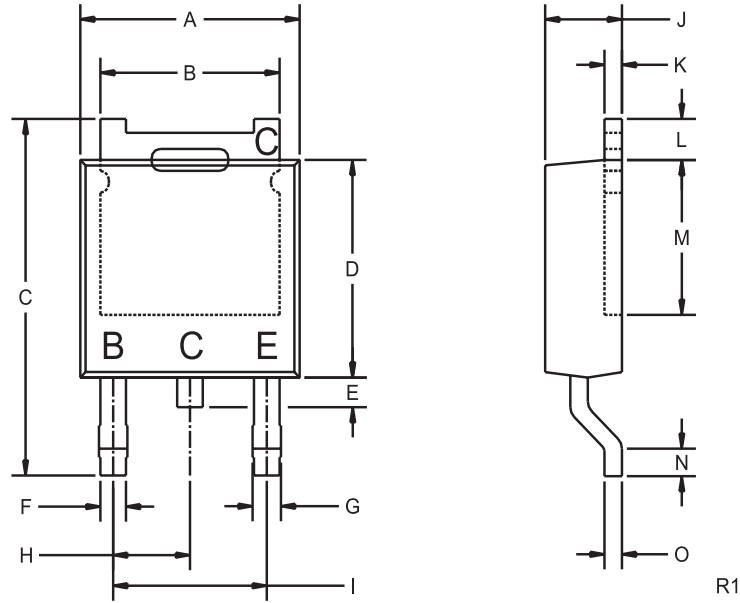
ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CEO}	V _{CE} =60V		50	μA
I _{CES}	V _{CE} =100V		20	μA
I _{EBO}	V _{EB} =5.0V		1.0	mA
BV _{CEO}	I _C =30mA	100		V
V _{CE(SAT)}	I _C =3.0A, I _B =375mA		1.2	V
V _{BE(ON)}	V _{CE} =4.0V, I _C =3.0A		1.8	V
h _{FE}	V _{CE} =4.0V, I _C =1.0A	25		
h _{FE}	V _{CE} =4.0V, I _C =3.0A	10	50	
f _T	V _{CE} =10V, I _C =500mA, f=1.0MHz	3.0		MHz
h _{fe}	V _{CE} =10V, I _C =500mA, f=1.0kHz	20		

R1 (26-September 2002)

**COMPLEMENTARY SILICON
POWER TRANSISTOR**

DPAK TRANSISTOR CASE - MECHANICAL OUTLINE



LEAD CODE:

- B) BASE
- C) COLLECTOR
- E) EMITTER
- C) COLLECTOR

**MARKING CODE:
FULL PART
NUMBER**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.250	0.265	6.35	6.73
B	0.205	0.215	5.21	5.46
C	0.374	0.409	9.50	10.40
D	0.235	0.245	5.97	6.22
E	0.025	0.040	0.64	1.02
F	0.025	0.035	0.64	0.88
G	0.030	0.045	0.76	1.14
H	0.090		2.28	
I	0.180		4.57	
J	0.086	0.094	2.19	2.38
K	0.018	0.023	0.46	0.58
L	0.040	0.050	1.02	1.27
M	0.170	-	4.32	-
N	0.020	-	0.51	-
O	0.018	0.023	0.46	0.58

DPAK TRANSISTOR (REV: R1)